

9.6A, 500V, 0.600 Ohm, N-Channel Power MOSFET

This is an N-Channel enhancement mode silicon gate power field effect transistor designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. This type can be operated directly from integrated circuits.

Formerly developmental type TA17435.

Ordering Information

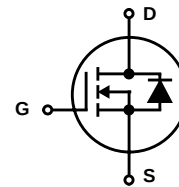
PART NUMBER	PACKAGE	BRAND
BUZ45	TO-204AA	BUZ45

NOTE: When ordering, use the entire part number.

Features

- 9.6A, 500V
- $r_{DS(ON)} = 0.600\Omega$
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device

Symbol



Packaging

JEDEC TO-204AA

